A high-re ectivity high-Q m icrom echanical B ragg-m irror

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W e report on the fabrication and characterization of a m icrom echanical oscillator consisting only of a free-standing dielectric B ragg m irror with high optical re ectivity and high m echanical quality. The fabrication technique is a hybrid approach involving laser ablation and dry etching. The m irror has a re ectivity of 99.6%, a m ass of 400ng, and a m echanical quality factor Q of approxim ately 10^4 . U sing this m icrom irror in a Fabry Perot cavity, a nesse of 500 has been achieved. This is an important step towards designing tunable high-Q high-nesse cavities on chip.

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M icrom echanical oscillators are today widely used in applications from therm al, infrared and chem ical to biological sensing [1]. This huge success is due to the fact that sensors based on m icro cantilevers can detect extremely small stimuli such as temperature and mass changes as well as sm all external forces [2]. A vailable devices can be placed in two categories based on their readout scheme. M icro electro-mechanical systems (MEMS) use a wide array of electronic coupling schemes to transduce m echanical energy into electronic signals, while m icro opto-mechanical systems (MOMS) are usually read out using an optic lever or a Fabry Perot interferom eter. For MOMS, the sensitivity or coupling strength is mainly dependent on both the mechanical quality and the re ectivity of the cantilever. By increasing the mechanical quality factor and using ultra-high re ectivity m aterials one can thus considerably increase the performance of such sensors. Ultimately, when all technical noise sources have been elim inated, quantum mechanics poses a limit in the sensitivity of such devices [3]. A \vdash though in today's sensor applications this quantum lim it has not yet been reached [4], a very close approach has been dem onstrated [5, 6].

W hile the re ectivity of a bulk dielectric or sem iconductorm aterial is, in general, quite low (typically around 50%), re ectivities of up to 98% can be achieved by depositing a thin m etallic layer on top of prede ned struc-

tures. If higher re ectivities are needed one has to use Bragg mirrors which consist of a stack of thin layers of m aterials with di erent refractive indices. Such m irrorm aterials are widely used and can reach re ectivities larger than 99.999% or, when used as m irrors in an optical cavity, a cavity nesse of > 106. High re ectivities have been achieved in MEMS tunable Fabry-Perot etalons, however with a very low mechanical quality Q typically well below 10 [7]. In this paper we report the fabrication and characterization of a high-quality mechanical beam oscillator consisting of a free-standing Bragg m irror with 99:6 0:1% re ectivity and of high 10⁴. In contrast to previous apmechanical quality Q proaches, where the re ectivity of Sim icrostructures is increased by coating them in a postprocessing step, we directly fabricate the microstructure out of a large-scale Bragg-m irror (See gure 1). This avoids the unwanted side e ects that typically arise during the coating procedure, such as bending due to therm alm ism atch [8]. The fabrication technique is based on pulsed-laser ablation of the coating, followed by dry-etching of the substrate underneath. Laser ablation is an interesting technique complementary to standard micro-fabrication methods, since, unlike wet etching or reactive ion etching, it does not depend on the chem ical reactivity of the material being patterned [9, 10]. Furtherm ore, the good spatial selectivity achieved with short laser pulses allows the local rem ovalofm aterial while it preserves the coating quality on the oscillator.

The low selectivity on material at high laser uences allow sablation of thick dielectric stacks of materials with di erent chem ical properties. The good control of the ablation depth permits well-de ned rem oval of the coating. To free the structure from the substrate, a very selec-

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3- dry undercut of Si substrate

5 - SEM picture of the cantilever

FIG. 1: The steps of the fabrication process: (1) The Si-Substrate coated with a high re ectivity bragg m intor is protected from debris of the ablation process with a thin layer of photoresist. U sing a simple in aging system the light from a F_2 laser ablates rectangular structures from the coating. The ablation is stopped as soon as the Si-Layer is reached.(2) The debris from ablation is rem oved together with the photoresist in a solvent bath. (3) U sing X eF₂ gas the silicon substrate is selectively etched, leading to an undercut of the beam . (4) The nal structure consists only of a freestanding B ragg m irror. (5) The oscillator is the bridge in the center. It is about 520 m long, 120 m wide and has a total thickness of about 2.4 m. The dark region of the surface corresponds to the region where the HR coating has not been undercut.

tive dry-etching m ethod was em ployed. It undercuts the patterned coating but does not etch it in any m easurablem anner. Following the description of the fabrication m ethod we present the experimental setup to characterize the optical and m echanical quality of the resulting structure. Subsequently we give a short summary and discussion of the obtained results.

The fabrication of the m icrom irrors starts from a standard polished silicon wafer on which 16 layers of T iD₂ and SiD₂ have been deposited to form a highly re ective (HR) B ragg m irror. This process, which has been optim ized to reduce tensile stress, was done by the coating com pany O LB G m bH. The nom inal re ectivity is 99.8% at a wavelength of 1064 nm.

Subsequently the coated wafer is patterned using laser ablation by projecting 193 nm ArF-laser radiation (1.3 $J=cm^2$, $_1 = 28$ ns, repetition rate 1 to 10 pps) via a m echanicalm ask (reduction optics 10.1). W ith the laser pulse length em ployed, the heat a ected zone (HAZ) was about 5 m. This is in reasonable agreem ent with estim ates of lateral heat di usion in the silicon substrate [9]. To protect the mirror from debris generated during laser ablation, the surface is coated with a thin layer of a soft-baked photoresist (Shipley S1813). A fler ablation this layer is dissolved in an ultrasonic bath of acetone. By putting the sample in a X eF₂ atm osphere the exposed Si substrate is etched rapidly [11] (1 m / min)



FIG. 2: (a) Sketch of the Measurement scheme. The laser is an ultrastable YAG Laser which delivers up to 1W continuous-wave laser light at 1064nm with 1 kHz linewidth. The laser is phase modulated via an electro-optic modulator (EOM) at 19 MHz. This frequency is chosen to be above the mechanical resonance frequencies, but within the cavity bandwidth.About 0.5 mW of this modulated light is used to pump the optical cavity. Using a PBS cube, we send part of the light re ected back from the cavity to a High-Speed In-GaAsphotodiode. By mixing the photocurrent with the opticalm odulation frequency and subsequent low -pass ltering we derive the Pound-D rever-H all (PDH) [13] error signal that is, to the storder, proportional to the cavity length. Feeding this signal to a P ID controller that drives a piezoelectric actuator the length of the cavity is stabilized at resonance. Due to the lim ited bandwidth of the control loop, the cavity length is kept constant at accoustic frequencies, while above the cut-o frequency of the PID controller the vibrations of the beam are still present in the error signal. Therefore feeding the error signal to a spectrum analyzer allow sus to monitor both cavity and m irror dynam ics. (b) Frequency spectrum of the PDH signal when the cavity is locked (red) and not locked (black). The trace re ects the position RMS noise of the cantilever. M arkers indicate m echanical resonance peaks (see text). The noise our corresponds to approximately 10 16 m = $\frac{1}{H}$ H z.

isotropically and very selectively in the ablated regions around and below the beam. The Si/SiO_2 selectivity of the etch is better than 1000:1 [12], and there is no m easurable etch of TiO_2 , which is the top layer of the coating. The etching is optically monitored in-situ, and is stopped as soon as the beam is fully underetched. The nalstructure consists of a free-standing beam of approxim ately 520 m length and a width of 120 m, which is m ade only out of the original 2.4 m thick B ragg-m irror coating surrounded by a mem brane of about half of its width. The total m ass of the beam, as calculated from its dimensions, is about 400ng. The uneven undercut of the structure depicted in gure 1 is most probably due to partial coverage of the silicon surface with other materials. Possible sources of contam ination are incomplete ablation, redeposition of ablated material or oxidation of the heated silicon surface in air, all of which can be avoided by ablating the coating in vacuum or deeper ablation.

The micro-mirror was characterized via Fabry-Perot interferom etry. We built a linear Fabry-Perot optical cavity with the beam as the highly-re ecting end mirror on one side and a massive input coupler mirror on the other side (see gure 2). The input-coupler is a concave m irror with radius of curvature R = 25 mm and a re ectivity of 99.4% for 1064nm radiation. The cavity was slightly shorter than 25 mm. The chip containing the micro-mirror was placed on a 3-axis translation stage for alignment and the optical beam was positioned on the oscillator. The size of the waist of the TEM $_{\rm 00}$ m ode of the cavity is around 20 m, which is much smaller than the width of the beam . The input m irror is placed on a piezoelectric transducer (PTZ) respectively to scan the length of the cavity. The whole cavity is placed in a vacuum cham ber with a pressure of p < 2 10⁵ m bar to avoid damping of the oscillations of the beam due to air friction. All experiments were performed at room temperature.

For readout, the cavity is locked via the Pound-D rever-Hall (PDH) method [13]. The PDH locking signal is sent to a P D controller, the output of which is sent to the PZT to control the ne length of the cavity at resonance (Fig.3). It is known that the intensity of the PDH error signal around resonance is proportional to the change in length of the cavity. As a consequence, the vibrational noise of the beam can be monitored with high accuracy via the spectrum of the PDH error signal [14]. The optical quality is characterized by measuring the nesse F of the cavity, which is related to the round-trip intensity loss via F = 2 = in the lim it of a high-nesse cavity. Wemeasured a nesse of 650 at non-undercut regions of the m irror and of around 500 on the beam, corresponding to overall round trip losses of 1% and 1.3% respectively (This includes the 0.6% insertion losses on the input coupler). To determ ine the re ectivity of the coating, we build a cavity using a region of the coating that is spaced a few mm from the ablated structures. In this regions we obtain a re ectivity of 99.6% (i.e. a m in in aldegradation from the nom inal value). The additional losses of 0.3% on the beam can be explained both by di raction losses and by imperfections introduced during laser ablation, in particular near the edges of the beam .

The mechanical quality factor is obtained via the frequency spectrum of the PDH signal while the cavity is locked at resonance with the input laser frequency. Severalm echanical resonance peaks can be detected within the range of 200 kH z to 5 M H z. Their frequencies m atch well with nite elements (FE) simulations of transverse vibrationalm odes (i.e. oscillations occur norm alto the surface) of a doubly clam ped beam under tensile stress, speci cally of a fundamental mode at 278kH z and its harm onics. We observe an additional splitting of each transversem ode into twom odes separated by a few kH z, which can be identified as modes with different torsional contributions.

A critical parameter for performing high-sensitivity m easurem ents with m ovable m icro-m irrors is their m echanical quality factor Q, which is a direct measure for the time scale of dissipation in an oscillating system . Q is de ned as the ratio between the resonance frequency and the full width at half maximum (FW HM) correspond to of the resonance peak. It is a crucial param eter for sensors as it lim its the sensitivity of all measurements. We isolated the lowest resonance at 278 kHz, which corresponds to the fundam ental transverse m ode of the beam . The measured Q-factor of this mode was around 9000, with a FW HM of around 32Hz. The Q-factor of higherorder m odes decreases m onotonically to around 2000 for the fourth transverse mode at 1.2M Hz, which is indicative for the presence of clamping losses (see for exam ple [2] and references therein). One should nally note that our method is not limited to the present parameter range but can in principle yield much higher re ectivity and Q. For example, the re ectivity can be increased by em ploying sophisticated state-of-the-art HR coatings as are typically used for gravitational wave detectors (yielding re ectivity of up to 99.9999%). A nother possibility is to use Silicon-On-Insulator (SO I) technology instead of plain silicon wafers. The dry etch would then undercut only the device layer and stop on the buried oxide. This could lead to more kinetically controlled etching, i.e. to a better control of the m em brane uniform ity, and hence to a more controlled resonance frequency and higher Q factor.

In conclusion, we have demonstrated a promising m ethod for the fabrication of m icrom echanical m irrors with high re ectivity, high m echanical quality, and low m ass. Such a Bragg m irror is the lightest HR beam that one can design since the coating itself constitutes all the m ass. W e have characterized its m echanical and optical properties by using thism icro-m irror in a Fabry-Perot interferom eter. The re ectivity of the m irror is in principle lim ited only by the intrinsic coating quality. The com – bination of high re ectivity, low m ass and high m echanicalquality m ake the fabricated m icro-m echanicalm irrors an excellent candidate for high-sensitivity measurem ents down to the quantum lim it. In addition, such structures m ay provide the possibility to study genuine quantum e ects involving m echanical system s [15, 16, 17, 18].

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